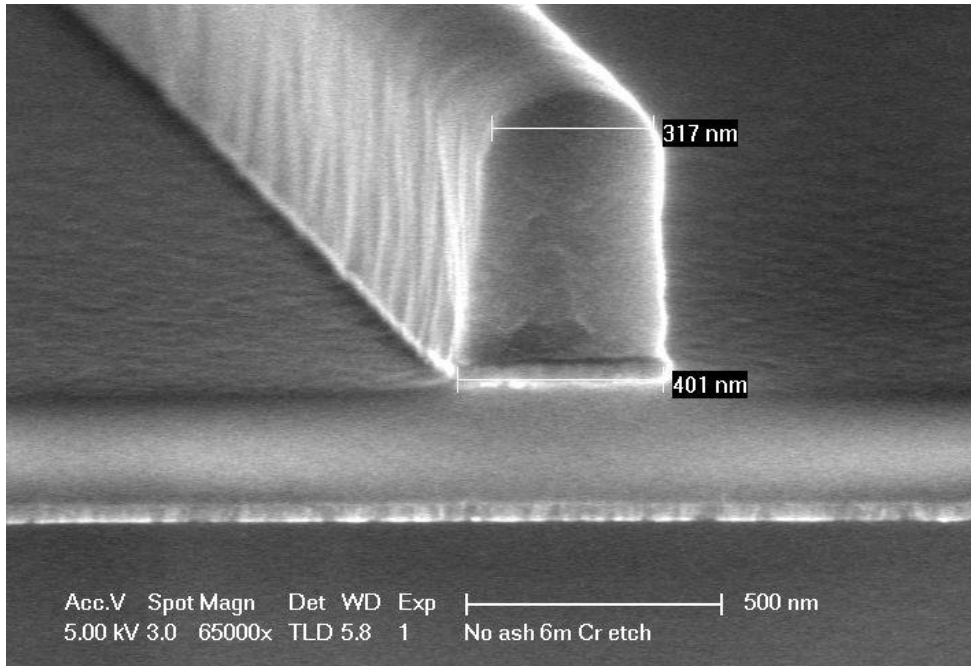


Recipe for Cr-trench

- 24 sccm Cl₂
- 6 sccm O₂
- 1.33 Pa
- 600 W ICP, 50 W Bias
- Etch Rate: ~36nm/min.
- SiO₂ hard Mask
- Small Undercut, sub-100nm features



G. Burek

PR Mask not removed

Recipe for Cr-mesa

- 26 sccm Cl₂
- 4 sccm O₂
- 1.0 Pa
- 400 W ICP, 15 W Bias
- Etch Rate: ~22 nm/min.
- PR Mask
- thick Cr-films (~100nm or thicker) can undercut